

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (currently amended): A compound semiconductor epitaxial substrate for use in a strain channel high electron mobility field effect transistor, comprising an InGaAs layer as a strain channel layer and an AlGaAs layer containing n-type impurities as an electron supplying layer, wherein said InGaAs layer has an emission peak wavelength at 77 K of 1030 nm or more and wherein said InGaAs layer has an electron mobility at 300 K of 8300 cm²/V·s or more.
2. (Original): The compound semiconductor epitaxial substrate according to claim 1, wherein GaAs layers are provided as spacer layers in contact with a top surface and a bottom surface of said InGaAs layer, respectively.
3. (Original): The compound semiconductor epitaxial substrate according to claim 2, wherein each of said GaAs layers has a thickness of 4 nm or more.
4. (canceled).

5. (withdrawn): A method for manufacturing a compound semiconductor epitaxial substrate that comprises an InGaAs layer as a strain channel layer and an AlGaAs layer containing n-type impurities as an electron supplying layer, wherein said InGaAs layer has an emission peak wavelength at 77 K of 1030 nm or more, said method comprising epitaxially growing each compound semiconductor layer by employing a metalorganic chemical vapor deposition (MOCVD) method.

6. (withdrawn): The method according to Claim 5, wherein GaAs layers are provided as spacer layers in contact with a top surface and a bottom surface of said InGaAs layer, respectively.

7. (withdrawn): The method according to Claim 6, wherein each of said GaAs layers has a thickness of 4 nm or more

8. (withdrawn): The method according to Claim 5, wherein said InGaAs layer has an electron mobility at 300 K of $8300 \text{ cm}^2/\text{V}\cdot\text{s}$ or more.